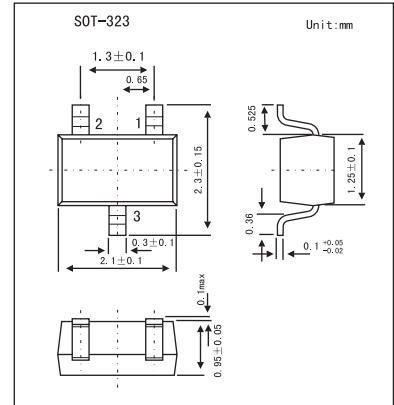


## Silicon Schottky Barrier Diode

## HSB88WA

## ■ Features

- Low reverse current, Low capacitance.
- CMPAK package is suitable for high density surface mounting and high speed assembly.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Reverse voltage	$V_R$	10	V
Average rectified current	$I_o$	15	mA
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	$V_F$	$I_F = 1 \text{ mA}$	0.35		0.42	V
		$I_F = 10 \text{ mA}$	0.50		0.58	
Reverse current	$I_R$	$V_R = 2 \text{ V}$			0.2	$\mu\text{A}$
		$V_R = 10 \text{ V}$			10	
Capacitance	$C$	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$			0.80	pF
Capacitance deviation	$\Delta C$	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$			0.10	pF
Forward voltage deviation	$\Delta V_F$	$I_F = 10 \text{ mA}$			10	mV
ESD-Capability (Note 1)		$C=200 \text{ pF}, R=0 \Omega$ Both forward and reverse direction 1 pulse.	30			V

Note

1. Failure criterion ;  $I_R \geq 0.4 \mu\text{A}$  at  $V_R = 2 \text{ V}$ 

## ■ Marking

Marking	C7
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